

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	141	(substrate semiconductor wafer silicon) and (etch\$6 same (hardmask (hard adj mask)) same (contact plug barrier) same capacitor same ((lower bottom first second upper top) adj electrode))	US-PGPUB; USPAT	OR	ON	2005/04/16 15:14
L2	72	etch\$6 and (hardmask (hard adj mask)) and (contact plug barrier) and capacitor and ((lower bottom first second upper top) adj electrode)	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/16 16:15
L3	1267	encapsulat\$6 and (capacitor ((lower bottom first second upper top) adj electrode))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/16 16:23
L4	63	L3 and (etch\$6 hardmask (hard adj mask))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/16 16:23
L5	5907	438/3.ccls. 438/240.ccls. 438/253.ccls. 438/396.ccls. 257/532.ccls.	US-PGPUB; USPAT	OR	OFF	2005/04/16 16:39
L6	148	L5 and ((etch\$6 hardmask (hard adj mask)) same encapsulat\$6)	US-PGPUB; USPAT	OR	ON	2005/04/16 16:39
L7	295	L5 and (etch\$6 same (hardmask (hard adj mask)) same (electrode contact plug barrier encapsulat\$6))	US-PGPUB; USPAT	OR	ON	2005/04/16 17:19
S1	5	("6351006" "20030008517" "20030119251" "6295195" "20020158278").PN.	US-PGPUB; USPAT	OR	OFF	2005/04/15 17:03
S2	4	ep-911871-\$.did. ep-1345258-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2005/04/15 16:05
S3	5907	438/3.ccls. 438/240.ccls. 438/253.ccls. 438/396.ccls. 257/532.ccls.	US-PGPUB; USPAT	OR	OFF	2005/04/15 17:09
S4	412	S3 and (etch\$6 same (hardmask (hard adj mask)))	US-PGPUB; USPAT	OR	ON	2005/04/15 17:10
S6	22	(substrate semiconductor wafer silicon) and (etch\$6 same (hardmask (hard adj mask)) same (contact plug barrier) same encapsulat\$6 same (capacitor ((lower bottom first second upper top) adj electrode)))	US-PGPUB; USPAT	OR	ON	2005/04/15 17:32

S7	413	(substrate semiconductor wafer silicon) and (etch\$6 same (hardmask (hard adj mask)) same (contact plug barrier) same (capacitor ((lower bottom first second upper top) adj electrode)))	US-PGPUB; USPAT	OR	ON	2005/04/15 17:18
S9	174	etch\$6 and (hardmask (hard adj mask)) and (contact plug barrier) and (capacitor ((lower bottom first second upper top) adj electrode))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/15 17:21
S11	0	S9 and encapsulat\$6	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/15 17:21
S12	1266	encapsulat\$6 and (capacitor ((lower bottom first second upper top) adj electrode))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/15 17:22
S14	298	S3 and (etch\$6 hardmask (hard adj mask)) and encapsulat\$6	US-PGPUB; USPAT	OR	ON	2005/04/15 17:24